



STI20N60M2-EP Information

Heisener.com

Part Number STI20N60M2-EP
Manufacturer STMicroelectronics

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 600V 13A TO-220

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

For Reference Only

Website: https://www.heisener.com
E-mail: salesdept@heisener.com

Request a Quote



Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









STI20N60M2-EP Specifications

Manufacturer Part Number ST120N60M2-EP Manufacturer STMicroelectronics Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series MDmesh? M2-EP FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 13A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 21.7nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 787pF @ 100V Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 110W (Tc) Rds On (Max) @ Id, Vgs 278 mOhm @ 6.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220 Package / Case TO-220-3		
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C13A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs21.7nC @ 10VInput Capacitance (Ciss) (Max) @ Vds787pF @ 100VVgs (Max)±25VFET Feature-Power Dissipation (Max)110W (Tc)Rds On (Max) @ Id, Vgs278 mOhm @ 6.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220Package / CaseTO-220-3	Package	TO-220-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C13A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs21.7nC @ 10VInput Capacitance (Ciss) (Max) @ Vds787pF @ 100VVgs (Max)±25VFET Feature-Power Dissipation (Max)110W (Tc)Rds On (Max) @ Id, Vgs278 mOhm @ 6.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220Package / CaseTO-220-3	Series	MDmesh? M2-EP
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Current - Continuous Drain (Id) @ 25°C13A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs21.7nC @ 10VInput Capacitance (Ciss) (Max) @ Vds787pF @ 100VVgs (Max)±25VFET Feature-Power Dissipation (Max)110W (Tc)Rds On (Max) @ Id, Vgs278 mOhm @ 6.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220Package / CaseTO-220-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs21.7nC @ 10VInput Capacitance (Ciss) (Max) @ Vds787pF @ 100VVgs (Max)±25VFET Feature-Power Dissipation (Max)110W (Tc)Rds On (Max) @ Id, Vgs278 mOhm @ 6.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220Package / CaseTO-220-3	Drain to Source Voltage (Vdss)	600V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 11.7nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 787pF @ 100V Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 110W (Tc) Rds On (Max) @ Id, Vgs 278 mOhm @ 6.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220 Package / Case TO-220-3	Current - Continuous Drain (Id) @ 25°C	13A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 787pF @ 100V Vgs (Max) ±25V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 278 mOhm @ 6.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220 Package / Case TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 787pF @ 100V Vgs (Max) ET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 278 mOhm @ 6.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220 Package / Case TO-220-3	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±25VFET Feature-Power Dissipation (Max)110W (Tc)Rds On (Max) @ Id, Vgs278 mOhm @ 6.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220Package / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	21.7nC @ 10V
FET Feature - To-220-3 FET Feature - To-220-3 FET Feature - To-220-1 Time Feature - To-220-1 Time Feature - To-220-1 Time Feature - To-220-1 Time Feature - To-220-1 To-220-	Input Capacitance (Ciss) (Max) @ Vds	787pF @ 100V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 278 mOhm @ 6.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220 Package / Case TO-220-3	Vgs (Max)	±25V
Rds On (Max) @ Id, Vgs278 mOhm @ 6.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220Package / CaseTO-220-3	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220 Package / Case TO-220-3	Power Dissipation (Max)	110W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220 Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	278 mOhm @ 6.5A, 10V
Supplier Device Package TO-220 Package / Case TO-220-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220
Report errors?	Package / Case	TO-220-3
		Report errors?

STI20N60M2-EP Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

STI20N60M2-EP Payment Methods



















STI20N60M2-EP Shipping Methods













If you have any question about STI20N60M2-EP, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com